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CORRECTION

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Correction: Low-energy interlayer phonon assisted carrier recombination in Z-scheme van der Waals heterostructures for photocatalysis

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Correction for 'Low-energy interlayer phonon assisted carrier recombination in Z-scheme van der Waals heterostructures for photocatalysis' by Hejin Yan et al., J. Mater. Chem. A, 2022, 10, 23744–23750, https://doi.org/10.1039/D2TA04935J.

The authors regret that there was an error repeated throughout the published manuscript. Throughout the article, including in the article's title and contents page description, the word "intralayer" mistakenly appeared instead of the correct word "interlayer". There are three exceptions to this:

- "[...] the CBM_{MoSe₂} to VBM_{WSi₂N₄} path will compete with a direct intralayer hopping from CBM_{MoSe₂} to VBM_{MoSe₂}." (lines 14–16, column 1, p. 23747).
 - "[...] besides direct intralayer charge recombination (from CBM_{TMD} to VBM_{TMD})." (lines 27 and 28, column 1, p. 23747).
- "[...] while the contribution from the intralayer recombination is found to be negligible." (line 30, column 1 to line 1, column 2, p. 23748).

In these three exceptions, "intralayer" appears correctly within the original published article. Everywhere else "intralayer" should be replaced by "interlayer".

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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